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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

E·XFI

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	115
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 40x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151zct6tr

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

The memory protection unit (MPU) improves system reliability by defining the memory attributes (such as read/write access permissions) for different memory regions. It provides up to eight different regions and an optional predefined background region.

Owing to its embedded ARM core, the STM32L151xC/C-A and STM32L152xC/C-A devices are compatible with all ARM tools and software.

#### Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L151xC/C-A and STM32L152xC/C-A devices embed a nested vectored interrupt controller able to handle up to 56 maskable interrupt channels (not including the 16 interrupt lines of ARM<sup>®</sup> Cortex<sup>®</sup>-M3) and 16 priority levels.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving*, higher-priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

# 3.3 **Reset and supply management**

#### 3.3.1 **Power supply schemes**

- V<sub>DD</sub> = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V<sub>DD</sub> pins.
- $V_{SSA}$ ,  $V_{DDA}$  = 1.65 to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL (minimum voltage to be applied to  $V_{DDA}$  is 1.8 V when the ADC is used).  $V_{DDA}$  and  $V_{SSA}$  must be connected to  $V_{DD}$  and  $V_{SS}$ , respectively.

#### 3.3.2 Power supply supervisor

The device has an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

The device exists in two versions:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V<sub>DD</sub> threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the V<sub>DD</sub> min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the



power ramp-up should guarantee that 1.65 V is reached on  $V_{\text{DD}}$  at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage ( $V_{REFINT}$ ) in Stop mode. The device remains in reset mode when  $V_{DD}$  is below a specified threshold,  $V_{POR/PDR}$  or  $V_{BOR}$ , without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the startup time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The device features an embedded programmable voltage detector (PVD) that monitors the  $V_{DD}/V_{DDA}$  power supply and compares it to the  $V_{PVD}$  threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when  $V_{DD}/V_{DDA}$  drops below the  $V_{PVD}$  threshold and/or when  $V_{DD}/V_{DDA}$  is higher than the  $V_{PVD}$  threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

#### 3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC\_CSR).

#### 3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using USART1, USART2 or USB. See Application note "STM32 microcontroller system memory boot mode" (AN2606) for details.



### 3.13 Ultra-low-power comparators and reference voltage

The STM32L151xC/C-A and STM32L152xC/C-A devices embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with fixed threshold
- One comparator with rail-to-rail inputs, fast or slow mode. The threshold can be one of the following:
  - DAC output
  - External I/O
  - Internal reference voltage (V<sub>REFINT</sub>) or a sub-multiple (1/4, 1/2, 3/4)

Both comparators can wake up from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1  $\mu$ A typical).

# 3.14 System configuration controller and routing interface

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM3 and TIM4 timer input captures. It also controls the routing of internal analog signals to ADC1, COMP1 and COMP2 and the internal reference voltage  $V_{\text{REFINT}}$ .

# 3.15 Touch sensing

The STM32L151xC/C-A and STM32L152xC/C-A devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 23 capacitive sensing channels distributed over 10 analog I/O groups. Both software and timer capacitive sensing acquisition modes are supported.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (glass, plastic...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. The capacitive sensing acquisition only requires few external components to operate. This acquisition is managed directly by the GPIOs, timers and analog I/O groups (see Section 3.14: System configuration controller and routing interface).

Reliable touch sensing functionality can be quickly and easily implemented using the free STM32L1xx STMTouch touch sensing firmware library.





Figure 6. STM32L15xRC-A LQFP64 pinout

1. This figure shows the package top view.

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	F	Pins							Pin function	IS
LQFP144	UFBGA132	LQFP100	LQFP64	WLCSP64	Pin name	Pin Type <sup>(1)</sup>	I / O structure	Main function <sup>(2)</sup> (after reset)	Alternate functions	Additional functions
7	C1	7	2	C8	PC13- WKUP2	I/O	FT	PC13	-	WKUP2/ RTC_TAMP1/ RTC_TS/ RTC_OUT
8	D1	8	3	B8	PC14- OSC32_IN <sup>(4)</sup>	I/O	тс	PC14	-	OSC32_IN
9	E1	9	4	B7	PC15- OSC32_OUT	I/O	тс	PC15	-	OSC32_OUT
10	D6	-	-	-	PF0	I/O	FT	PF0	-	-
11	D5	-	-	-	PF1	I/O	FT	PF1	-	-
12	D4	-	-	-	PF2	I/O	FT	PF2	-	-
13	E4	-	-	-	PF3	I/O	FT	PF3	-	-
14	F3	-	-	-	PF4	I/O	FT	PF4	-	-
15	F4	-	-	-	PF5	I/O	FT	PF5	-	-
16	F2	10	-	-	$V_{SS_5}$	S	-	$V_{SS_5}$	-	-
17	G2	11	-	-	V <sub>DD_5</sub>	S	-	$V_{DD_5}$	-	-
18	G3	-	-	-	PF6	I/O	FT	PF6	TIM5_CH1/TIM5_ETR	ADC_IN27
19	G4	-	-	-	PF7	I/O	FT	PF7	TIM5_CH2	ADC_IN28/ COMP1_INP
20	H4	-	-	-	PF8	I/O	FT	PF8	TIM5_CH3	ADC_IN29/ COMP1_INP
21	J6	-	-	-	PF9	I/O	FT	PF9	TIM5_CH4	ADC_IN30/ COMP1_INP
22	-	-	-	-	PF10	I/O	FT	PF10	-	ADC_IN31/ COMP1_INP
23	F1	12	5	D8	PH0- OSC_IN <sup>(5)</sup>	I/O	тс	PH0	-	OSC_IN
24	G1	13	6	D7	PH1- OSC_OUT <sup>(5)</sup>	I/O	тс	PH1	-	OSC_OUT
25	H2	14	7	C7	NRST	I/O	RST	NRST	_	-
26	H1	15	8	E8	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP

# Table 8. STM32L151xC/C-A and STM32L152xC/C-A pin definitions (continued)





Symbol	Parameter	Conditions		f <sub>HCLK</sub> [MHz]	Тур	Max (1)	Unit
			Range3.	1	290	500	
			V <sub>CORE</sub> =1.2 V	2	505	750	μA
			VOS[1:0]=11	4	955	1200	
		$f_{HSE} = f_{HCLK}$ up to 16MHz.	Range2, V <sub>CORE</sub> =1.5 V	4	1.15	1.6	
		included $f_{HSE} = f_{HCLK}/2$ above		8	2.3	1200 1.6 2.9 5.2 5.3.5 6.5 6.5 m/	
		16 MHz (PLL ON) <sup>(2)</sup>	VOS[1:0]=10	16	4.25	5.2	mA
			Range1, V <sub>CORE</sub> =1.8 V VOS[1:0]=01	8	2.65	3.5	
I <sub>DD (Run</sub>	Supply current in			16	5.35	6.5	
from	Run mode code executed from Flash			32	10.5	12	
Flash)			Range2, V <sub>CORE</sub> =1.5 V VOS[1:0]=10	16	4.35	5.2	
			Range1, V <sub>CORE</sub> =1.8 V VOS[1:0]=01	32	10.5	12.3	
		MSI clock, 65 kHZ	Range3	0.065	46	130	μA
		MSI clock, 524 kHZ	V <sub>CORE</sub> =1.2 V	0.524	160	250	
		MSI clock, 4.2 MHZ	VOS[1:0]=11	4.2	965	1200	

#### Table 17. Current consumption in Run mode, code with data processing running from Flash

1. Guaranteed by characterization results, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).



Symbol	Parameter	Conditions		f <sub>HCLK</sub>	Тур	Max	Unit
			Range3.	1	230	470	μA
		fuer = fuer up to 16 MHz.	V <sub>CORE</sub> =1.2 V	2	415	780	
			VOS[1:0]=11	4	800	1200	
			Pange?	4	0.935	1.5	
		included $f_{HSE} = f_{HCLK}/2$ above	V <sub>CORE</sub> =1.5 V	8	1.9	3	
		16MHz (PLL ON)(')	VOS[1:0]=10	16	3.75	5	mA
			Range1, V <sub>CORE</sub> =1.8 V VOS[1:0]=01	8	2.25	3.5	
	Supply current in Run mode code executed from RAM			16	4.45	5.55	
<sup>I</sup> DD (Run from RAM)				32	9.05	10.9	
		HSI clock source (16 MHz)	Range2, V <sub>CORE</sub> =1.5 V VOS[1:0]=10	16	3.75	4.8	
			Range1, V <sub>CORE</sub> =1.8 V VOS[1:0]=01	32	8.95	11.7	
		MSI clock, 65 kHZ	Range3	0.065	43.5	100	
		MSI clock, 524 kHZ	V <sub>CORE</sub> =1.2 V	0.524	135	215	μA
		MSI clock, 4.2 MHZ	VOS[1:0]=11	4.2	835	1100	

### Table 18. Current consumption in Run mode, code with data processing running from RAM

1. Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).



- Data based on differential I<sub>DD</sub> measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f<sub>HCLK</sub> = 32 MHz (range 1), f<sub>HCLK</sub> = 16 MHz (range 2), f<sub>HCLK</sub> = 4 MHz (range 3), f<sub>HCLK</sub> = 64kHz (Low-power run/sleep), f<sub>APB1</sub> = f<sub>HCLK</sub>, f<sub>APB2</sub> = f<sub>HCLK</sub>, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling.
- 2. HSI oscillator is OFF for this measure.
- 3. In Low-power sleep and run mode, the Flash memory must always be in power-down mode.
- 4. Data based on a differential Ibb measurement between ADC in reset configuration and continuous ADC conversion (HSI consumption not included).
- Data based on a differential IDD measurement between DAC in reset configuration and continuous DAC conversion of VDD/2. DAC is in buffered mode, output is left floating.
- 6. Including supply current of internal reference voltage.

#### 6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is the MSI oscillator in the range configured before entering Stop mode
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under the conditions summarized in Table 13.



#### Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a lowspeed external clock source, and under the conditions summarized in Table 13.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f <sub>LSE_ext</sub>	User external clock source frequency		1	32.768	1000	kHz
V <sub>LSEH</sub>	OSC32_IN input pin high level voltage		0.7V <sub>DD</sub>	-	V <sub>DD</sub>	V
V <sub>LSEL</sub>	OSC32_IN input pin low level voltage	-	$V_{SS}$	-	0.3V <sub>DD</sub>	v
t <sub>w(LSEH)</sub> t <sub>w(LSEL)</sub>	OSC32_IN high or low time		465	-	-	ne
t <sub>r(LSE)</sub> t <sub>f(LSE)</sub>	OSC32_IN rise or fall time		-	-	10	115
C <sub>IN(LSE)</sub>	OSC32_IN input capacitance	-	-	0.6	-	pF

Table 27. Low-speed external user clock characteristics<sup>(1)</sup>

1. Guaranteed by design.



#### Figure 15. Low-speed external clock source AC timing diagram

#### High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in Table 28. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).



- t<sub>SU(LSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.
- Note: For  $C_{L1}$  and  $C_{L2}$ , it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 17).  $C_{L1}$  and  $C_{L2}$ , are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ .

Load capacitance  $C_L$  has the following formula:  $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$  where  $C_{stray}$  is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

**Caution:** To avoid exceeding the maximum value of  $C_{L1}$  and  $C_{L2}$  (15 pF) it is strongly recommended to use a resonator with a load capacitance  $C_L \leq 7$  pF. Never use a resonator with a load capacitance of 12.5 pF.

**Example:** if the user chooses a resonator with a load capacitance of  $C_L = 6 \text{ pF}$  and  $C_{stray} = 2 \text{ pF}$ , then  $C_{L1} = C_{L2} = 8 \text{ pF}$ .



#### Figure 17. Typical application with a 32.768 kHz crystal

# 6.3.16 Communications interfaces

## I<sup>2</sup>C interface characteristics

The device I<sup>2</sup>C interface meets the requirements of the standard I<sup>2</sup>C communication protocol with the following restrictions: SDA and SCL are not "true" open-drain I/O pins. When configured as open-drain, the PMOS connected between the I/O pin and V<sub>DD</sub> is disabled, but is still present.

The I<sup>2</sup>C characteristics are described in *Table 47*. Refer also to *Section 6.3.13: I/O port characteristics* for more details on the input/output ction characteristics (SDA and SCL).

Symbol	Parameter	Standar I <sup>2</sup> C <sup>(</sup>	<b>d mode</b> 1)(2)	Fast mode	Unit	
		Min	Max	Min	Max	
t <sub>w(SCLL)</sub>	SCL clock low time	4.7	-	1.3	-	
t <sub>w(SCLH)</sub>	SCL clock high time	4.0	-	0.6	-	μο
t <sub>su(SDA)</sub>	SDA setup time	250	-	100	-	
t <sub>h(SDA)</sub>	SDA data hold time	-	3450 <sup>(3)</sup>	-	900 <sup>(3)</sup>	
t <sub>r(SDA)</sub> t <sub>r(SCL)</sub>	SDA and SCL rise time	-	1000	-	300	ns
t <sub>f(SDA)</sub> t <sub>f(SCL)</sub>	SDA and SCL fall time	-	300	-	300	
t <sub>h(STA)</sub>	Start condition hold time	4.0	-	0.6	-	
t <sub>su(STA)</sub>	Repeated Start condition setup time	4.7	-	0.6	-	μs
t <sub>su(STO)</sub>	Stop condition setup time	4.0	-	0.6	-	μs
t <sub>w(STO:STA)</sub>	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs
Cb	Capacitive load for each bus line	-	400	-	400	pF
t <sub>SP</sub>	Pulse width of spikes that are suppressed by the analog filter	0	50 <sup>(4)</sup>	0	50 <sup>(4)</sup>	ns

Table 47. I<sup>2</sup>C characteristics

1. Guaranteed by design.

 f<sub>PCLK1</sub> must be at least 2 MHz to achieve standard mode I<sup>2</sup>C frequencies. It must be at least 4 MHz to achieve fast mode I<sup>2</sup>C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I<sup>2</sup>C fast mode clock.

3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

4. The minimum width of the spikes filtered by the analog filter is above t<sub>SP(max)</sub>.



#### **Electrical characteristics**

Symbol	Parameter	Test conditions	Min <sup>(3)</sup>	Тур	Max <sup>(3)</sup>	Unit
ET	Total unadjusted error		-	2	4	
EO	Offset error	$2.4 \text{ V} \leq \text{V}_{\text{DDA}} \leq 3.6 \text{ V}$	-	1	2	
EG	Gain error	$2.4 \text{ V} \le \text{V}_{\text{REF+}} \le 3.6 \text{ V}$ $f_{\text{ADC}} = 8 \text{ MHz}$ , $\text{R}_{\text{ADM}} = 50 \Omega$	-	1.5	3.5	LSB
ED	Differential linearity error	$T_A = -40$ to 105 °C	-	1	2	
EL	Integral linearity error		-	1.7	3	
ENOB	Effective number of bits		9.2	10	-	bits
SINAD	Signal-to-noise and distortion ratio	2.4 V ≤ V <sub>DDA</sub> ≤ 3.6 V V <sub>DDA</sub> = V <sub>REF+</sub> f <sub>ADC</sub> = 16 MHz, R <sub>AIN</sub> = 50 Ω	57.5	62	-	
SNR	Signal-to-noise ratio	$T_A = -40$ to 105 °C	57.5	62	-	dB
THD	Total harmonic distortion	Finput=10KH2	-	-70	-65	
ENOB	Effective number of bits		9.2	10	-	bits
SINAD	Signal-to-noise and distortion ratio	$V_{DDA} = V_{REF+}$ $f_{ADC} = 8 MHz \text{ or } 4 MHz, R_{AIN} = 50 \Omega$	57.5	62	-	
SNR	Signal-to-noise ratio	$T_A = -40$ to 105 °C	57.5	62	-	dB
THD	Total harmonic distortion	Finput-IOKIZ	-	-70	-65	
ET	Total unadjusted error		-	4	6.5	
EO	Offset error	$2.4 \text{ V} \leq \text{V}_{\text{DDA}} \leq 3.6 \text{ V}$	-	2	4	
EG	Gain error	1.8 V $\leq$ V <sub>REF+</sub> $\leq$ 2.4 V fade = 4 MHz. Rain = 50 $\Omega$	-	4	6	LSB
ED	Differential linearity error	$T_{A} = -40$ to 105 °C	-	1	2	
EL	Integral linearity error		-	1.5	3	
ET	Total unadjusted error		-	2	3	
EO	Offset error	$1.8 \text{ V} \leq \text{V}_{\text{DDA}} \leq 2.4 \text{ V}$	-	1	1.5	
EG	Gain error	1.8 V $\leq$ V <sub>REF+</sub> $\leq$ 2.4 V fade = 4 MHz. Rain = 50 $\Omega$	-	1.5	2	LSB
ED	Differential linearity error	$T_{A} = -40$ to 105 °C	-	1	2	
EL	Integral linearity error		-	1	1.5	

# Table 56. ADC accuracy<sup>(1)(2)</sup>

1. ADC DC accuracy values are measured after internal calibration.

ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents. Any positive injection current within the limits specified for  $I_{INJ(PIN)}$  and  $\Sigma I_{INJ(PIN)}$  in Section 6.3.12 does not affect the ADC accuracy. 2.

3. Guaranteed by characterization results.



# 7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

# 7.1 LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package information



Figure 31. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package outline

1. Drawing is not to scale.





Figure 32. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package recommended footprint

1. Dimensions are in millimeters.

#### Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity

DocID026119 Rev 6



# 7.2 LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package information



Figure 34. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package outline

1. Drawing is not to scale.

Table 66. LQPF100,	14 x 14 mm,	100-pin low-profile	quad flat	package	mechanical
		data			

Symbol		millimeters		inches <sup>(1)</sup>				
Symbol	Min	Тур	Мах	Min	Тур	Max		
А	-	-	1.600	-	-	0.0630		
A1	0.050	-	0.150	0.0020	-	0.0059		
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571		
b	0.170	0.220	0.270	0.0067	0.0087	0.0106		
С	0.090	-	0.200	0.0035	-	0.0079		
D	15.800	16.000	16.200	0.6220	0.6299	0.6378		
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591		
D3	-	12.000	-	-	0.4724	-		
E	15.800	16.000	16.200	0.6220	0.6299	0.6378		
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591		



(continuou)									
Symbol		millimeters		inches <sup>(1)</sup>					
Symbol	Min	Тур	Мах	Min	Тур	Мах			
E3	-	7.500	-	-	0.2953	-			
е	-	0.500	-	-	0.0197	-			
К	0°	3.5°	7°	0°	3.5°	7°			
L	0.450	0.600	0.750	0.0177	0.0236	0.0295			
L1	-	1.000	-	-	0.0394	-			
CCC	-	-	0.080	-	-	0.0031			

# Table 67. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data(continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.



# Figure 38. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package recommended footprint

1. Dimensions are in millimeters.



#### Marking of engineering samples

The following figure gives an example of topside marking orientation versus ball A1 identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity



# 7.5 WLCSP64, 0.4 mm pitch wafer level chip scale package information



1. Drawing is not to scale.



			uala			
Symbol		millimeters			inches <sup>(1)</sup>	
	Min	Тур	Max	Min	Тур	Max
А	0.540	0.570	0.600	0.0205	0.0224	0.0236
A1	-	0.190	-	-	0.0075	-
A2	_	0.380	_	-	0.0150	_

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Figure 46. Thermal resistance suffix 6





# 7.6.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.



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